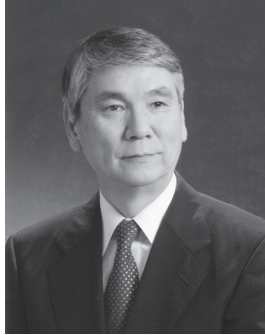


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最終学歴

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昭和48年3月	東北大学大学院工学研究科金属材料工学専攻修士課程修了
昭和51年3月	東北大学大学院工学研究科金属材料工学専攻博士課程修了

職歴

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昭和52年4月	東北大学工学部助手
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平成4年5月	東北大学素材工学研究所教授
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平成24年3月	東北大学を定年退職

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受賞

- | | |
|-------|---|
| 平成5年 | 日本金属学会功績賞 |
| 平成15年 | 米国 TMS, Extraction and Processing Science Award |
| 平成18年 | 日本金属学会谷川ハリス賞 |
| 平成18年 | (財)本多記念会本多フロンティア賞 |
| 平成20年 | 大韓金属材料学会ポスター発表論文優秀賞 |

学会等における活動

1. 資源・素材学会評議員（平成8年4月～14年3月）
2. 日本金属学会評議員（平成8年3月～12年3月，平成13年3月～17年3月，平成18年3月～平成24年3月）
3. 日本金属学会理事（平成18年3月～20年3月，平成22年3月～24年3月）
4. 日本金属学会東北支部長（平成17年4月～19年3月）
5. 日本金属学会欧文誌編集委員長（平成18年4月～19年3月）
6. Materials Transaction 誌編集委員長（平成18年4月～19年3月）
7. 日本金属学会副会長（平成19年4月～20年3月）
8. International Advisory Committee（平成21年～22年）APAC-SILICIDE 2010
（Asia-Pacific Conference on Semiconducting Silicides Science and Technology Towards Sustainable Optoelectronics）

社会における活動

1. 日本学術振興会「超高純度材料における表面安定化と初期酸化」
研究開発専門委員会委員長（平成10年7月～13年6月）
2. 日本学術振興会産学研究協力委員会161委員会委員（平成10年4月～）
3. 文部科学省科学技術政策研究所科学技術動向研究センター専門調査員
（平成14年4月～）
4. 電気磁気材料研究所評議員（平成6年4月～12年3月）
5. 電気磁気材料研究所理事（平成12年4月～22年6月）
6. 経済産業省製造産業局非鉄金属課、非鉄金属技術開発施策事後評価検討委員会委員
（平成15年4月～6月）

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